Silicon Carbide Schottky Diode

V _{RRM}	1200V
IF (135°C)	16A
Qc	54.1nC



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and Zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

- Package: TO-220AC Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, halogen-free
- Terminals: Tin plated leads
- Polarity: As marked

■Maximum Ratings (T_c **=**25°C Unless otherwise specified)

PARAMTETER	SYMBOL	UNIT	VALUE
Device marking code			D112010PG1
Reverse voltage (repetitive peak) @ T _j =25°C	V _{RRM}	V	1200
Reverse voltage (Surge Peak) @ Tj=25°C	V _{RSM}	V	1200
Reverse voltage (DC) @ T _j =25°C	V _{DC}	V	1200
Continuous forward current @ T _c =25°C			33
Continuous forward current @ T _c =135°C	I _F	A	16
Continuous forward current @ T _c =157°C			10
Non-repetitive peak forward surge current @ T _c =25°C, tp=10ms, Half Sine Wave	I _{FSM}	А	85
Power Dissipation@ T₀=25°C	_	w	192
Power Dissipation@ T _c =110°C	Ρ _{τοτ}		83
i ² t Value@ Tc=25°C ,tp=10ms	∫i²dt	A ² S	36
Operating junction and Storage temperature range	T _j ,T _{stg}	°C	-55 to +175



Electrical Characteristics

PARAMTETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.
Ferrurad uphane days	V _F	V	I _F =10A, T _j =25°C	1.51	1.65
Forward voltage drop		v	I _F =10A, T _j =175°C	2.25	2.7
	1		V _R =1200V, T _j =25°C	1	15
Reverse leakage current	I _R	μA	V _R =1200V, T _j =175°C	39	-
Total capacitive charge	Q _C	nC	V_R =800V, T _j =25°C , QC=J ₀ ^{VR} C(V)dV	54.1	
			V _R =0V, f=1MHZ	768.3	-
Total capacitance	С	pF	V _R =400V, f=1MHZ	51.7	-
			V _R =800V, f=1MHZ	37.2	-
Capacitance Stored Energy	Ec	μJ	V _R =800V	13.8	-

■Thermal Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Thermal resistance	$R_{_{ ext{ hetaJ-C}}}$	°C/W	0.78

■Characteristics (Typical)

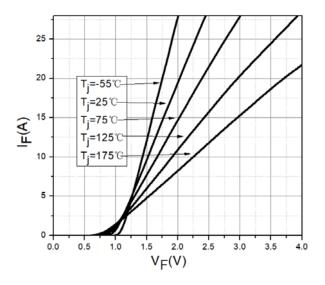


Figure 1. Forward Characteristics

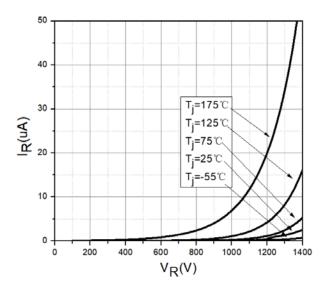


Figure2. Reverse Characteristic

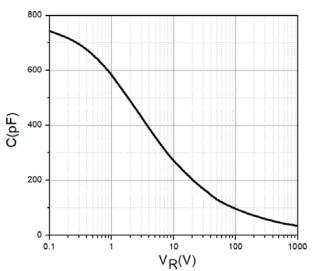


Figure 3. Capacitance vs. Reverse Voltage

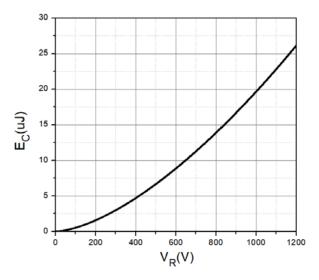


Figure 5. Capacitance Stored Energy

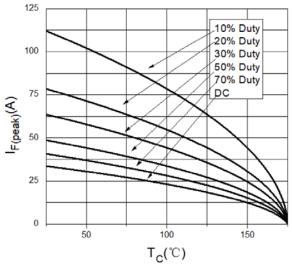
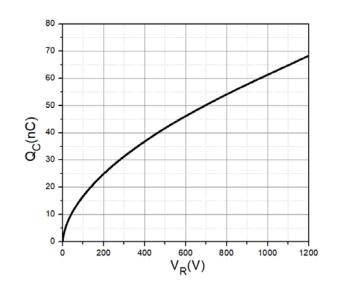


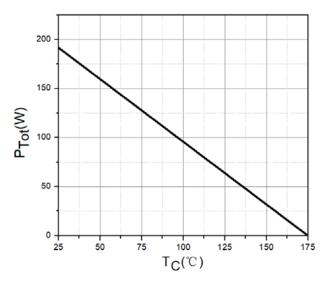
Figure 7. Current Derating

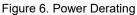


RoHS

COMPLIANT

Figure 4. Total Capacitance Charge vs. Reverse Voltage





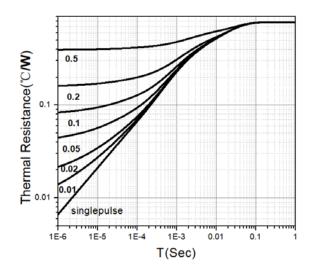
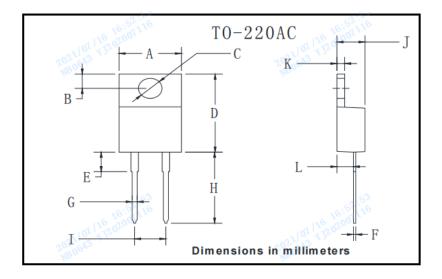


Figure 8. Transient Thermal Impedance



Outline Dimensions



TO-220AC				
Dim	Min	Max		
Α	9.5	10.9		
В	2.22	3.27		
С	3.34	4.31		
D	14.5	15.5		
E	3.16	4.46		
F	0.28	0.64		
G	0.68	0.94		
Н	13.06	14.62		
1	4.55	5.60		
J	4.04	5.1		
К	1.14	1.4		
L	2.14	3.19		



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